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This is a Request for Continued Examination (RCE) under 37 CFR 1.114 of the above-identified application

REQUEST

FOR

CONTINUED EXAMINATION (RCE) TRANSMITTAL

Address to: Commissioner for Patents Box RCE Washington, DC 20231

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Application Number	10/006,334
Filing Date	December 3, 2001
First Named Inventor	KAMESH V. GADEPALLY
Art Unit	2818 710706
Examiner Name	QUOC DINH HOANG . BRUI
Attorney Docket Number	NSC1-G0610 [P04402 P01]4

Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8,
1. Submission required under 37 CFR §1.114 a. □ Previously submitted i. □ Consider the amendment(s) reply under 37 CFR §1.116 previously filled on
i. RCE fee required under 37 CFR §1.17(e) ii. Extension of time fee (37 CFR §§1.136 and 1.17)
 iii. ☐ Other b. ☒ Check in the amount of \$ 750.00 enclosed c. ☐ Payment by credit card (Form PTO-2038 enclosed) WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED

	SIGNATURE OF APPLICANT, AT	TORNEY, OR AG	ENT REQUIRED	
Name (Print / Type) Signature	ALFRED A. EQUITZ	Registration No. (Attorney / Agent)		30,922
		Date	April 3, 2003	

CERTIFICATE OF MAILING OR TRANSMISSION

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Name (Print / Type) Marsha A. Townsend

Signature Moksha A. Toronsenel Date April 3, 2003

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

KAMESH V. GADEPALLY

Application No. 10/006,334

Filed: December 3, 2001

For: METHOD FOR MANUFACTURING

AN INTEGRATED CIRCUIT STRUCTURE WITH LIMITED SOURCE SALICIDATION Group Art Unit: 2818

Examiner: QUOC DINH HOANG

RESPONSE TO FINAL OFFICE ACTION

400 Montgomery St., Suite 1110 San Francisco, CA 94104 (415) 433-2250

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231, on April 3, 2003.

GIRARD & EQUITZ LLP

Date: 04/03/03

By: Marsha Ann Townsend

Box RCE Commissioner for Patents Washington, DC 20231

Sir:

This is in response to the final Office Action mailed on February 5, 2003, in the referenced application and is being filed with a Request for Continued Examination of the application. Please amend the application and consider the following remarks.

IN THE SPECIFICATION:

Amend lines 10-13 on page 7 to read as follows (the attached appendix sets forth the amended section of the specification with markings showing the differences between the original text and the text as hereby amended):

accordance with the present invention have been performed. Silicon gates 120 and 122 (typical thickness being in the range between 1500 and 4000 angstroms) overlie the gate oxide layer 110 of MOS transistor structures 104 and 106, respectively. Silicon gates 120 and 122 can be made from either

